

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	14	257/e21.632	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/11 06:14
L5	3	257/e21.633	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/11 06:14
S1	2523	nmos and pmos and sidewall spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/11 04:53
S2	1585	S1 and ion implant\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 17:35
S3	795	S2 and polysilicon gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 17:35
S4	5834	shallow junction	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 17:36
S5	242	S2 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 17:36
S6	105	S5 and nmos same (arsenic or phosphorus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 17:37

EAST Search History

S7	89	S5 and nmos same (arsenic or phosphorus) and pmos same boron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 19:13
S8	286	(438/230).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 17:48
S9	607	(438/231).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 17:47
S10	1	"5527722".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:18
S11	1	"5498556".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:19
S12	1	"5491099".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:23
S13	2	("6255152").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/09 18:24
S14	10	"6255152"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 18:24
S15	1	"6157064".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:27
S16	1	"6028339".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:29
S17	1	"5759885".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 18:29
S18	1	"5234850".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 19:09
S19	1	"5759885".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 19:10
S20	1	"6028339".PN.	USPAT; USOCR	ADJ	ON	2006/12/09 19:13

EAST Search History

S21	584	shallow junction and nmos and pmos	USPAT; USOCR	ADJ	ON	2006/12/09 19:13
S22	280	S4 and nmos same (arsenic or phosphorus) and pmos same boron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 19:14
S23	143	S4 and nmos same (arsenic or phosphorus) and pmos same boron and sidewall with spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 19:14
S24	104	S4 and nmos same (arsenic or phosphorus) and pmos same boron and sidewall spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 19:14
S25	208	S4 and nmos same (arsenic or phosphorus) and pmos same boron and sidewall and implant\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/12/09 19:15